

# General Purpose Transistor

## NPN Silicon

# NST3904MX2

### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

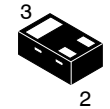
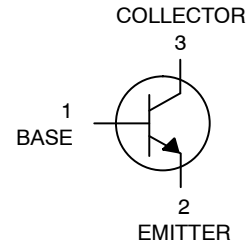
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	40	Vdc
Collector – Base Voltage	$V_{CBO}$	60	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous (Note 1)	$I_C$	200	mAdc
Collector Current – Peak (Note 1)	$I_{CM}$	900	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

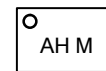
Characteristic	Symbol	Max	Unit
Total Power Dissipation (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	165 1.39	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	720	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	590 4.93	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	203	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. Reference SOA Curve
2. Surface-mounted on FR4 board using a  $0.6\text{ mm}^2$ , 2 oz. Cu pad
3. Surface-mounted on FR4 board using a  $100\text{ mm}^2$ , 2 oz. Cu pad



X2DFN3 (1.0 x 0.6 mm)  
CASE 714AC

### MARKING DIAGRAM



AH = Specific Device Code  
M = Date Code

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NST3904MX2T5G	X2DFN3 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NST3904MX2

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	–	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	–	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	–	50	nAdc

### ON CHARACTERISTICS (Note 4)

DC Current Gain (I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)	H <sub>FE</sub>	40 70 100 60 30	– – 300 – –	–
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)	V <sub>CE(sat)</sub>	– –	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)	V <sub>BE(sat)</sub>	0.65 –	0.85 0.95	Vdc

### SMALL – SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	f <sub>T</sub>	250	–	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	4.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	8.0	pF
Input Impedance (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>ie</sub>	1.0	10	kΩ
Voltage Feedback Ratio (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>re</sub>	0.5	8.0	X 10 <sup>-4</sup>
Small – Signal Current Gain (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	–
Output Admittance (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	40	μmhos
Noise Figure (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 100 μAdc, R <sub>S</sub> = 1.0 k ohms, f = 1.0 kHz)	NF	–	5.0	dB

### SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = –0.5 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)	t <sub>d</sub>	–	35	ns
Rise Time		t <sub>r</sub>	–	35	
Storage Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)	t <sub>s</sub>	–	210	ns
Fall Time		t <sub>f</sub>	–	50	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

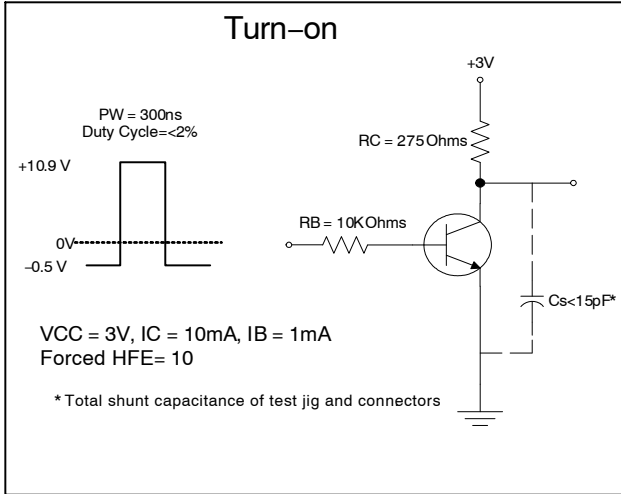


Figure 1. Delay and Rise Time Equivalent Test Circuit

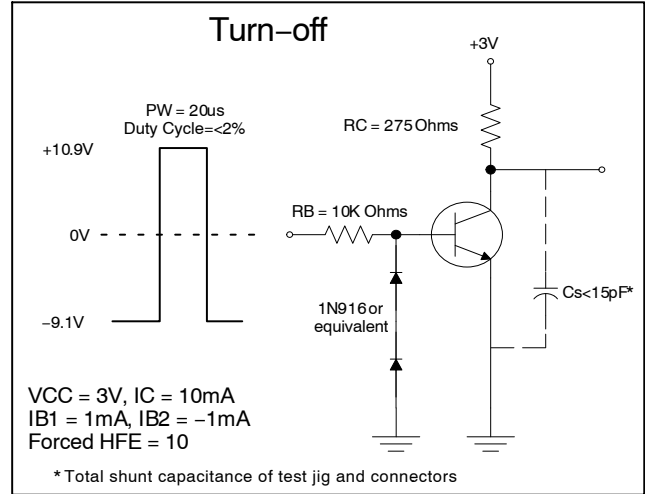


Figure 2. Storage and Fall Time Equivalent Test Circuit

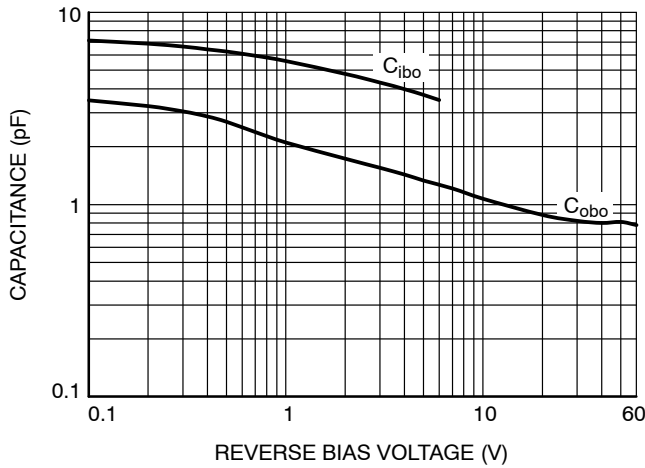


Figure 3. Capacitance

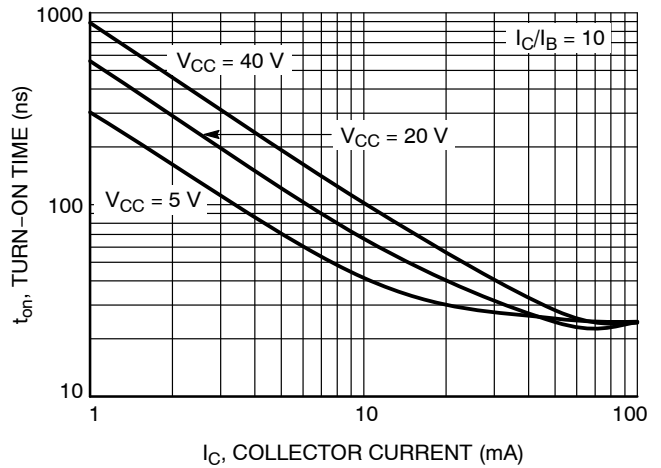


Figure 4. Turn-On Time

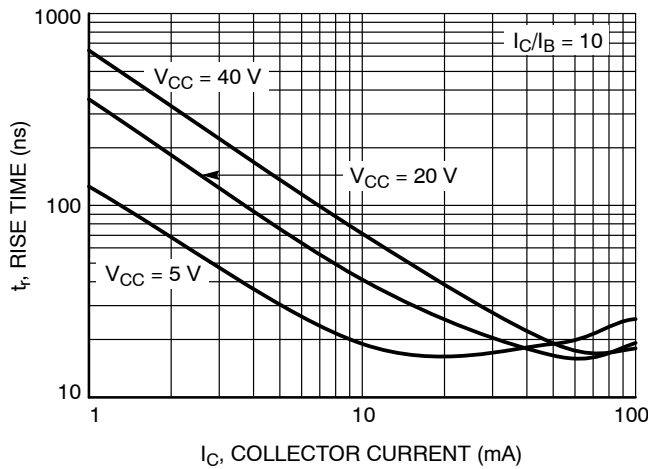


Figure 5. Rise Time

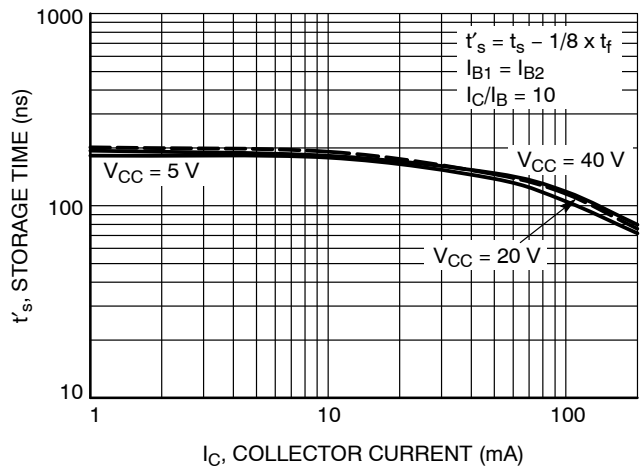


Figure 6. Storage Time

TYPICAL CHARACTERISTICS

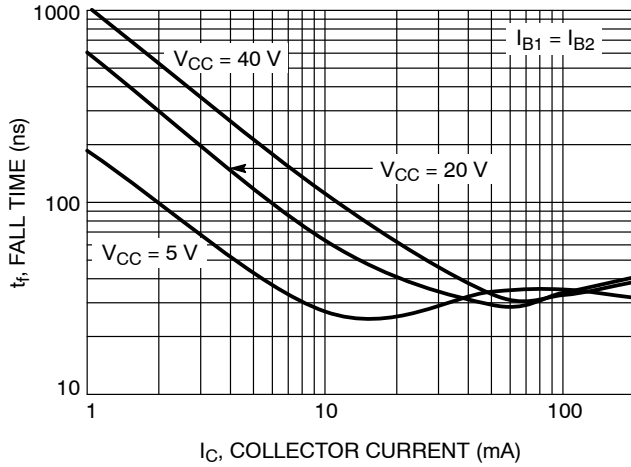


Figure 7. Fall Time

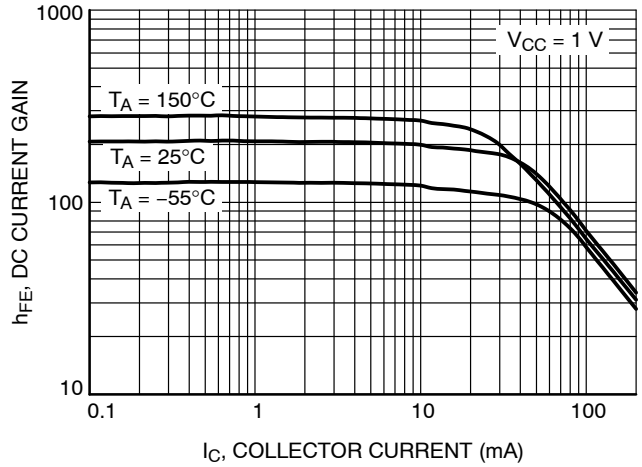


Figure 8. DC Current Gain

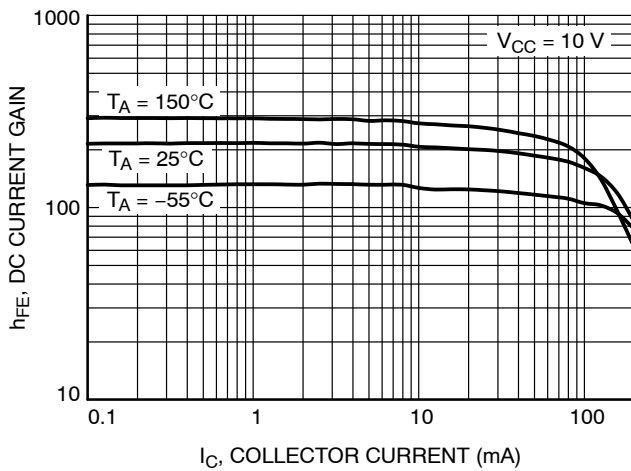


Figure 9. DC Current Gain

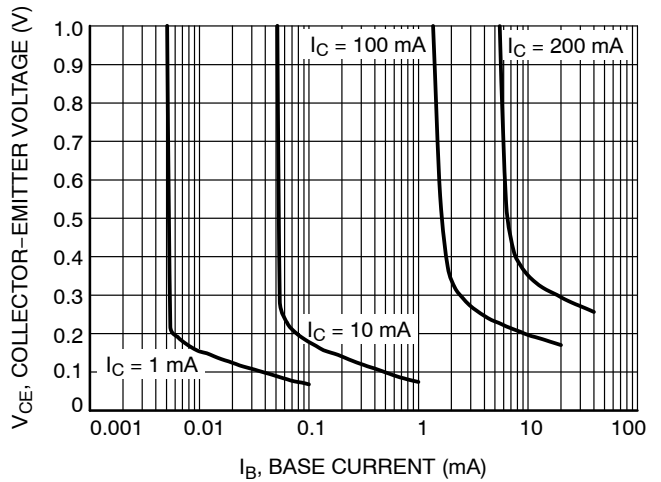


Figure 10. Collector Saturation Region

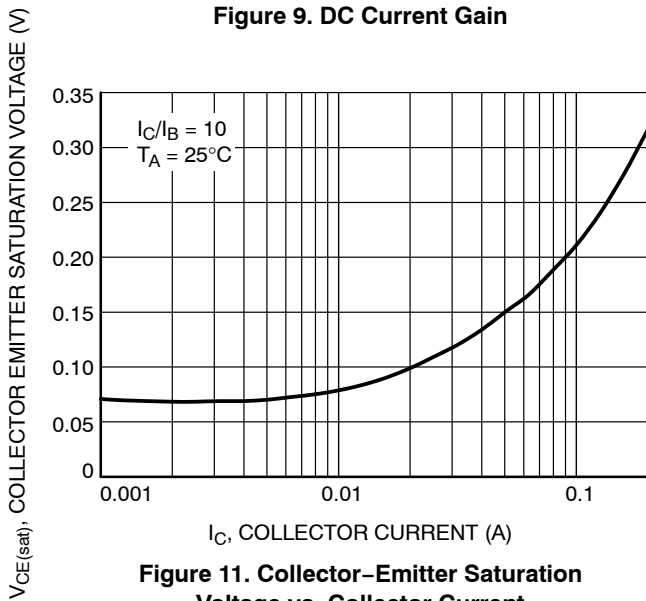


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

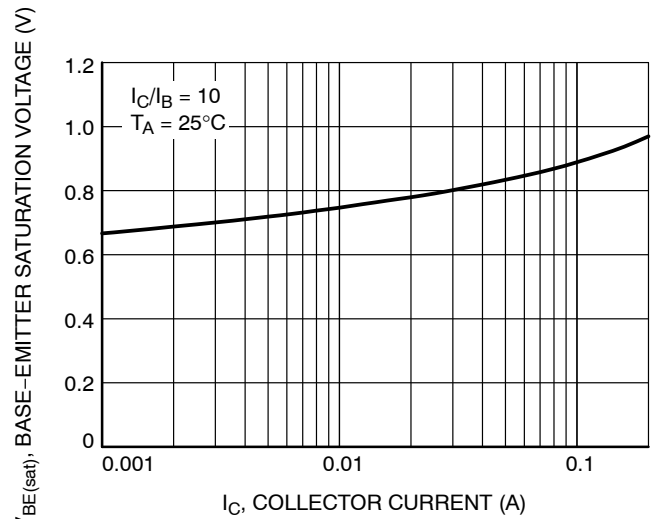


Figure 12. Base-Emitter Saturation Voltage vs. Collector Current

# NST3904MX2

## TYPICAL CHARACTERISTICS

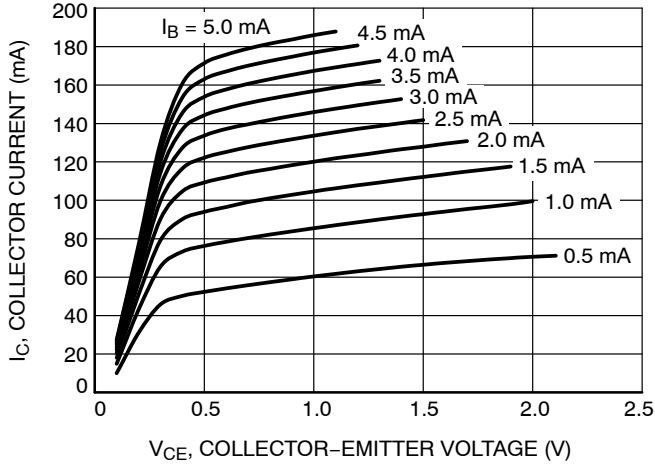


Figure 13. Collector Current vs. Collector-Emitter Voltage

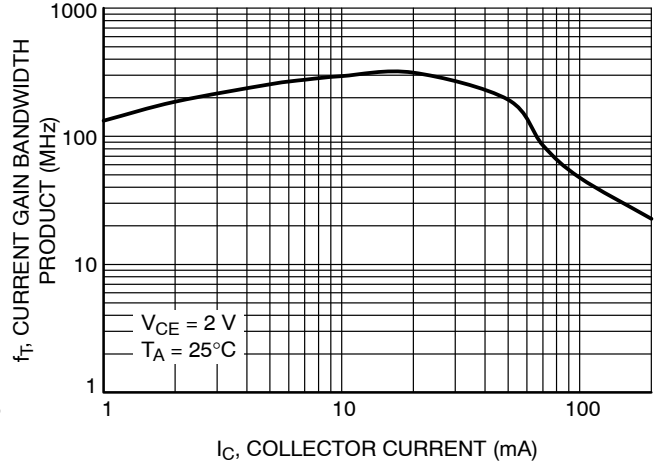


Figure 14. Current Gain Bandwidth vs. Collector Current

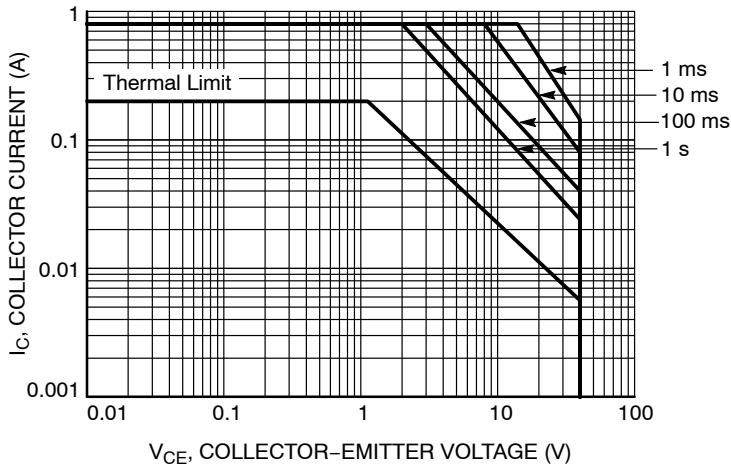
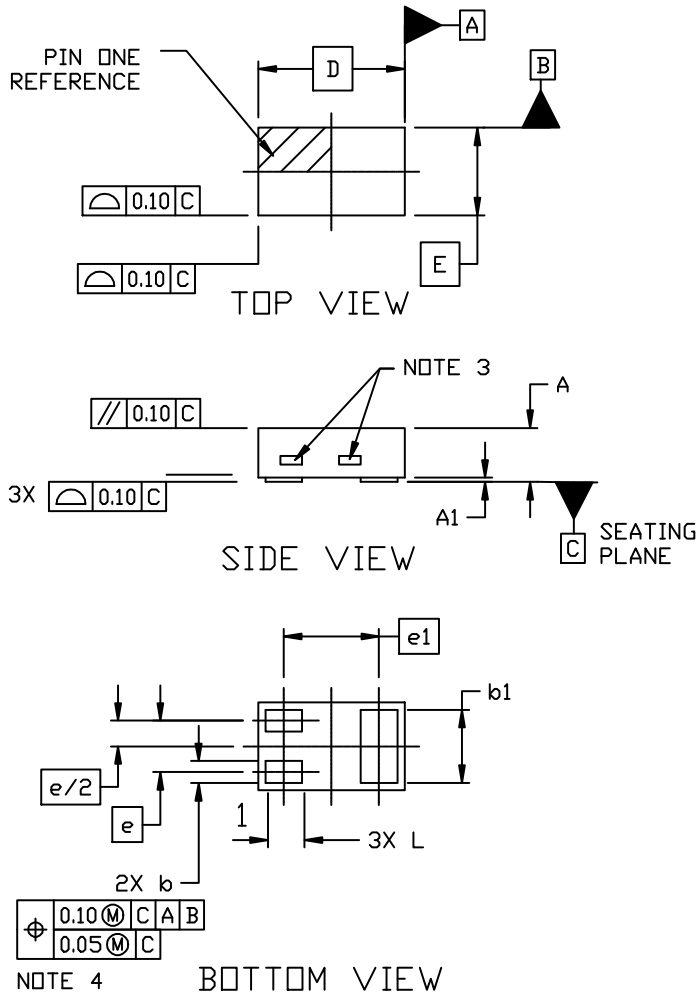


Figure 15. Safe Operating Area

# NST3904MX2

## PACKAGE DIMENSIONS

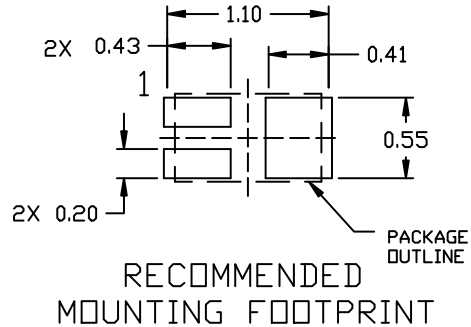
X2DFN3 1.0x0.6, 0.35P  
CASE 714AC  
ISSUE A



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. EXPOSED COPPER ALLOWED AS SHOWN.
4. ALL PAD LOCATIONS CONTROLLED WITH THIS POSITIONAL TOLERANCE.

DIM	MILLIMETERS		
	MIN.	MAX.	MAX.
A	0.34	0.37	0.40
A1	0.00	---	0.05
b	0.10	0.15	0.20
b1	0.45	0.50	0.55
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	0.35 BSC		
e1	0.65 BSC		
L	0.20	0.25	0.30



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